INTERNATIONAL RECTIFIER TOR



1N1199A,1N3670A SERIES

12 Amp Medium Power Silicon Rectifier Diodes

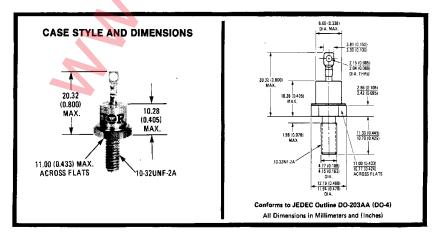
Major Ratings and Characteristics

Series	1N1199A 1N3670A	Units	
I _{F(AV)}	12*	A	
@ MAX. T _C	150*	°C	
^I FSM			
@ 50 Hz	230	Α	
@ 60 Hz	240*	^ (
I ² t			
@ 50 Hz	260	▲ A ² s	
@ 60 Hz	240	A-3	
™ _C .	-65° C* to 200° C	°C	
V _{RRM} range	50° - 1000°	V	

Description/Features

- Voltage ratings from 50 to 1,000 volts
- High surge capability
- Low thermal impedance
- High temperature rating
- Can be supplied as JAN and JAN-TX devices in accordance with MIL-S-19500/260

*JEDEC registered value.



VOLTAGE RATINGS

	V _{RRM} — Mex. Repetitive Peak Reverse Voltage (V)	V _{R(RMS)} - Max. RMS Reverse Voltage (V)_	V _{RSM} - Max. Non-Repetitive Peak Reverse Voltage (V)	V _R — Max. Direct Reverse Voltage (V)
Part Number 1	T _C = -65° C to 200° C	T _C = -65°C to 200°C	T _C = 0° C to 200° C	T _C ≈ -65°C to 200°C
1N1199A	50*	35*	100*	50°
1N1200A	100°	70°	200*	100*
1N1201A	150*	105*	300*	150*
1N1202A	200*	140*	350*	200*
1N1203A	300*	210*	450*	300*
1N1204A	400°	280*	600*	400*
1N1205A	500°	350*	700°	500°
1N1206A	600*	420°	800*	600*
1N3670A	700*	490	900*	700*
1N3671A	800*	560	1000*	800*
1N3672A	900*	630	1100*	900*
1N3673A	1000°	700	1200*	1000+

Basic part number indicates cathode-to-case. For anode-to-case, add "R" to part number, e.g., 1N1199RA.

ELECTRICAL SPECIFICATIONS

		1N1199A 1N3670A	Units	Conditions	
F(AV) Max. average forward current		12*	А	180° sinusoidal conduction	
	@ T _C max. =		°C		
(FSM	IFSM Max. peak one-cycle non-repetitive surge current		0° A	Half cycle 50 Hz sine wave or 6 ms rectangular pulse Following any rated load	
				Half cycle 60 Hz sine wave or 5 ms rectangular pulse condition and with rated V RRM reapplied	
				Half cycle 50 Hz sine wave or 6 ms rectangular pulse Following any rated load	
				Half cycle 60 Hz sine wave or 5 ms rectangular pulse condition and with VRRM applied following surge = 0	
t²t	I ² t Max. I ² t for fusing	260		t = 10ms With rated V _{RRM} applied following	
		240	A ² s	t = 8.3ms surge, initial T _J = 200°C	
	Max. l ² t for individual	370		t = 10ms With V _{RRM} = 0 following surge, initial T _J = 200° C	
	device fusing	340			
l²√t	Max, $ ^2\sqrt{t}$ for individual device fusing	3715	A²√s	t = 0.1 to 10ms, V _{RRM} = 0 following surge	
V _{FM}	Max. peak forward voltage	1.35*	٧	I _{F(AV)} = 12A (38A peak), T _C = 25°C	
R(AV)	Max, average reverse current VRRM = 50	3.0*	ļ	Mex. rated I _{F{AV}} and T _C	
	= 100	2.5*			
	= 150	2.25*	mA	Note: Max. peak reverse current, I _{RM} , under same conditions ≈ 2 x rated I _{R(AV)} .	
	= 200	2.0*		INC. F.	
	= 300	1.75*			

^{*}JEDEC registered value.

¹⁾ I2t for time $t_{\rm X} \approx I^2 \sqrt{t} + \sqrt{t_{\rm X}}$



ELECTRICAL SPECIFICATIONS (Continued)

	1N1199A 1N3670A	Units	Conditions
R(AV) Max. average reverse current (Continued) VRRM = 400	1.5*		
= 500	1.25*		Max. rated I _{F(AV)} and T _C
= 600	1.0*	mA	Note: Max. peak reverse current, IRM, under
= 700	0.9*	111/2	· · · · · · · · · · · · · · · · · · ·
= 800	0.8*	same conditions ≈ 2 x rated	same conditions $\approx 2 \times \text{rated } I_{R(AV)}$.
= 900	0.7*		
= 1000	0.6*		

THERMAL-MECHANICAL SPECIFICATIONS

T _C	Max. operating case temperature range		-65* to 200*	°C	
T _{stg}	Max. storage temperature range		-65* to 200*	°C	
RthJC Max. internal thermal resistance, junction-to-case		2.0*	deg. C/W	DC operation	
R _{thCS}	S Thermal resistance, case-to-sink		0.5	deg. C/W	Mounting surface flat, smooth, and greased.
Т	T Mounting torque				
	Mi	n.	1.36 (12)		Torque applied to nut, Non-Jubricated threads.
	Max. Min. Max. Min.		1.69 (15)		rorque applied to hut, Norridoricated threads.
			1.07 (9.45)	N·m	Torque applied to nut. Lubricated threads.
			1.30 (11.55)	(lbf-in)	Torque applied to flut. Eubricated tiricads.
			1.17 (10.35)		Torque applied to device case.
	Ma	Χ.	1.43 (12.65)		Lubricated threads.
wt	Approximate weight		7.0 (0.25)	g (oz.)	
	Case style		DO-203AA (DO-4)		JEDEC

^{*}JEDEC registered value.

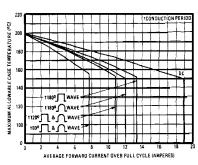


Fig. 1 - Average Forward Current Vs. Maximum
Allowable Case Temperature

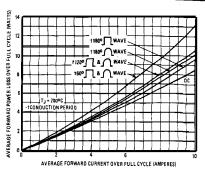


Fig. 2 — Maximum Low Level Forward Power Loss
Vs. Average Forward Current

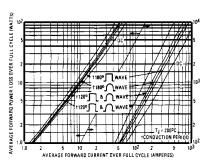


Fig. 3 — Maximum High Level Forward Power Loss Vs. Average Forward Current

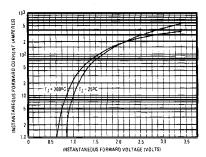


Fig. 4 – Maximum Forward Voltage Vs. Forward Current

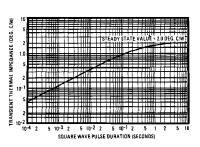


Fig. 5 — Maximum Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

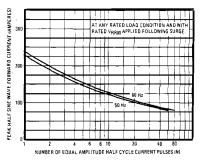


Fig. 6 — Maximum Non-Repetitive 50 Hz Surge Current Vs. Number of Current Pulses